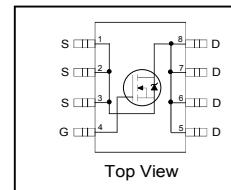


**Features**

- Advanced Planar Technology
- Low On-Resistance
- Logic Level Gate Drive
- Dynamic dv/dt Rating
- 150°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to T<sub>jmax</sub>
- Lead-Free, RoHS Compliant
- Automotive Qualified \*



<b>V<sub>DSS</sub></b>	<b>60V</b>
<b>R<sub>DS(on)</sub></b> typ.	<b>20mΩ</b>
	<b>max.</b> <b>26mΩ</b>
<b>I<sub>D</sub></b>	<b>7.0A</b>



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

**Description**

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRF7478Q	SO-8	Tape and Reel	4000	AUIRF7478QTR

**Absolute Maximum Ratings**

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
V <sub>DS</sub>	Drain-Source Voltage	60	V
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	7.0	A
I <sub>D</sub> @ T <sub>A</sub> = 70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	5.6	
I <sub>DM</sub>	Pulsed Drain Current ①	56	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Maximum Power Dissipation ④	2.5	W
	Linear Derating Factor	0.02	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Thermally Limited) ②	140	mJ
I <sub>AR</sub>	Avalanche Current ①	4.2	A
dv/dt	Peak Diode Recovery dv/dt ⑥	3.7	V/ns
T <sub>J</sub>	Operating Junction and	-55 to + 150	°C
T <sub>STG</sub>	Storage Temperature Range		

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
R <sub>θJL</sub>	Junction-to-Drain Lead	—	20	°C/W
R <sub>θJA</sub>	Junction-to-Ambient ④	—	50	

HEXFET® is a registered trademark of Infineon.

\*Qualification standards can be found at [www.infineon.com](http://www.infineon.com)

**Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

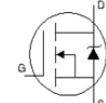
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{DSS}}$	Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
$\Delta V_{(\text{BR})\text{DSS}}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.065	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(\text{on})}$	Static Drain-to-Source On-Resistance	—	20	26	$\text{m}\Omega$	$V_{GS} = 10V, I_D = 4.2\text{A}$ ③
		—	23	30		$V_{GS} = 4.5V, I_D = 3.5\text{A}$ ③
$V_{GS(\text{th})}$	Gate Threshold Voltage	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
$g_{fs}$	Forward Trans conductance	17	—	—	S	$V_{DS} = 50V, I_D = 4.2\text{A}$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	$\mu\text{A}$	$V_{DS} = 48V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 48V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	$\text{nA}$	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$

**Dynamic Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

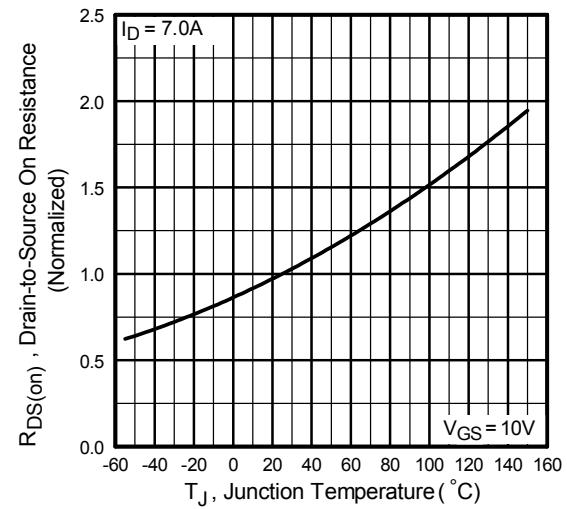
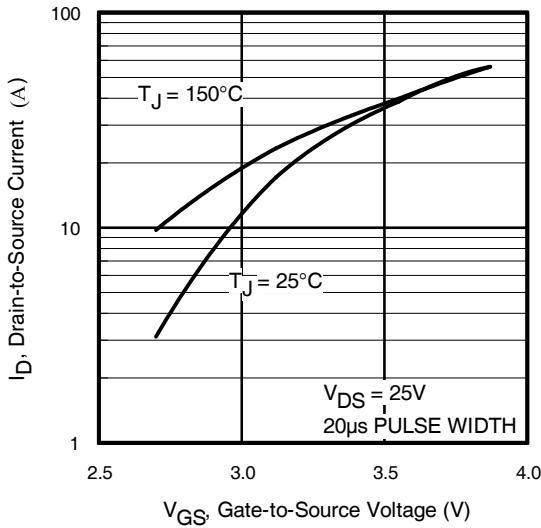
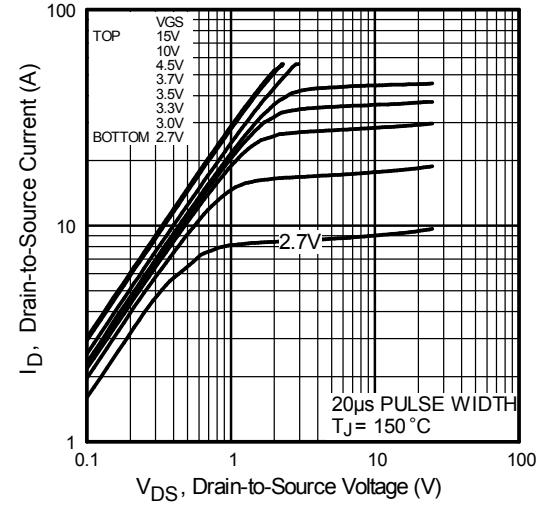
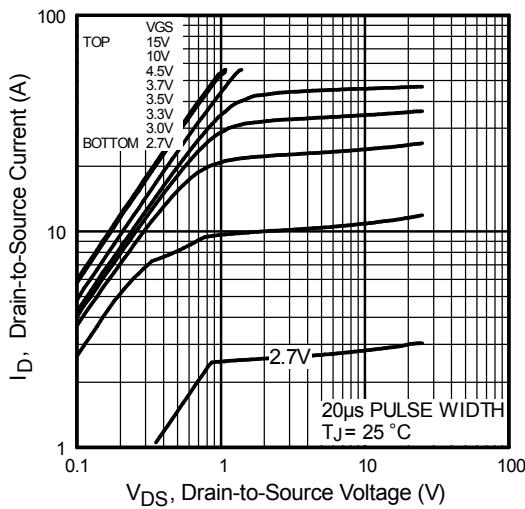
$Q_g$	Total Gate Charge	—	21	31	nC	$I_D = 4.2\text{A}$
$Q_{gs}$	Gate-to-Source Charge	—	4.3	—		$V_{DS} = 48V$
$Q_{qd}$	Gate-to-Drain Charge	—	9.6	—		$V_{GS} = 4.5V$
$t_{d(on)}$	Turn-On Delay Time	—	7.7	—	ns	$V_{DD} = 30V$
$t_r$	Rise Time	—	2.6	—		$I_D = 4.2\text{A}$
$t_{d(off)}$	Turn-Off Delay Time	—	44	—		$R_G = 6.2\Omega$
$t_f$	Fall Time	—	13	—		$V_{GS} = 10V$ ③
$C_{iss}$	Input Capacitance	—	1740	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	300	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	37	—		$f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	1590	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	220	—		$V_{GS} = 0V, V_{DS} = 48V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	410	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 48V$ ⑤

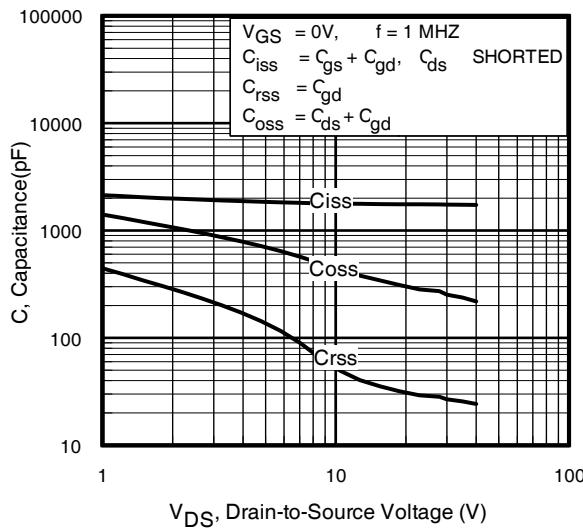
**Diode Characteristics**

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_s$	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	56		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 4.2\text{A}, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	52	78	ns	$T_J = 25^\circ\text{C}, I_F = 4.2\text{A}, di/dt = 100\text{A}/\mu\text{s}$ ③
$Q_{rr}$	Reverse Recovery Charge	—	100	150	nC	

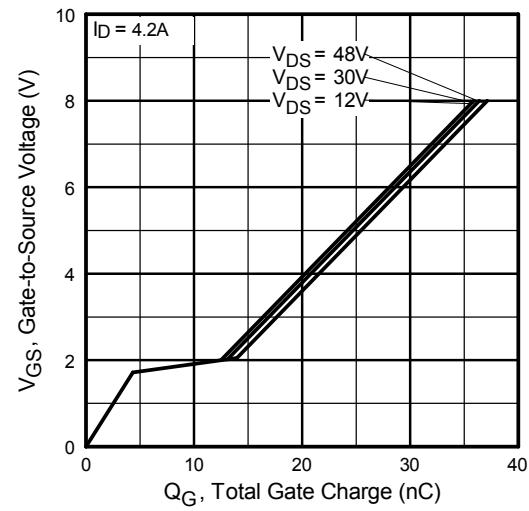

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 16\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 4.2\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ When mounted on 1" in square copper board.
- ⑤  $C_{oss}$  eff. is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑥  $I_{SD} \leq 4.2\text{A}$ ,  $di/dt \leq 160\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(\text{BR})\text{DSS}}$ ,  $T_J \leq 150^\circ\text{C}$ .

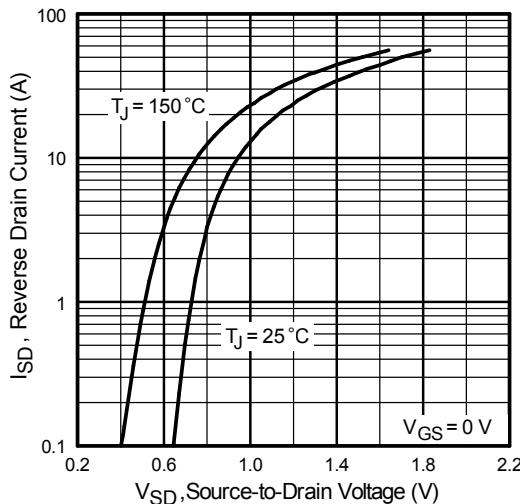




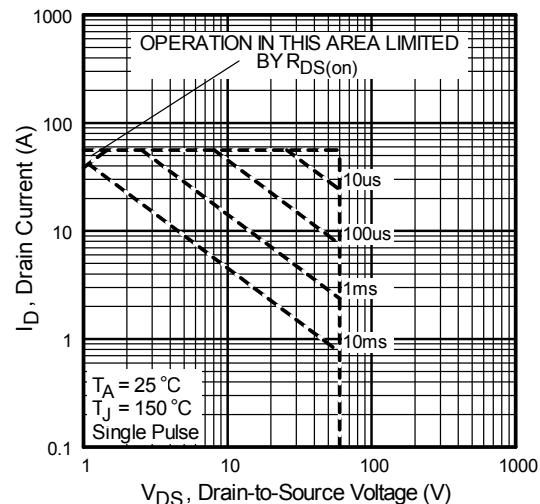
**Fig 5.** Typical Capacitance vs.  
Drain-to-Source Voltage



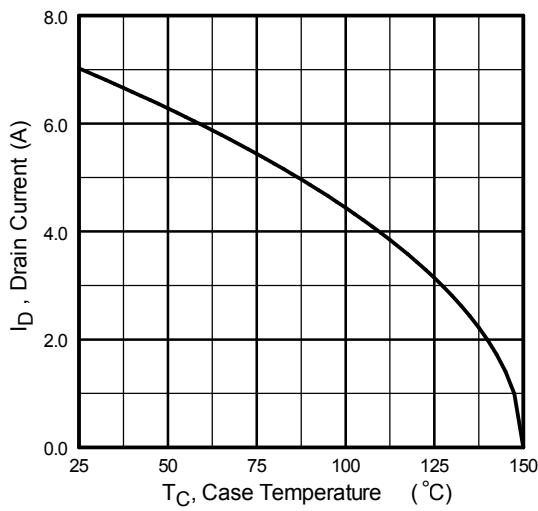
**Fig 6.** Typical Gate Charge vs.  
Gate-to-Source Voltage



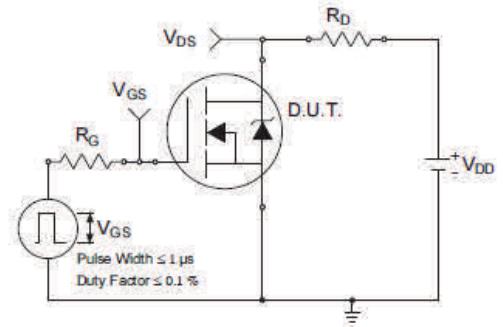
**Fig. 7** Typical Source-to-Drain Diode  
Forward Voltage



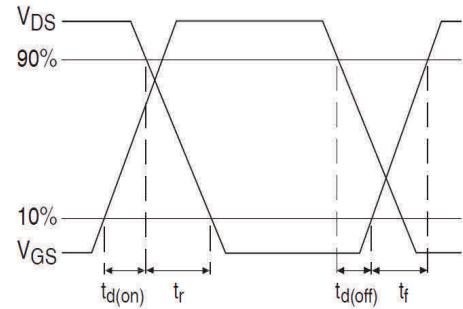
**Fig 8.** Maximum Safe Operating Area



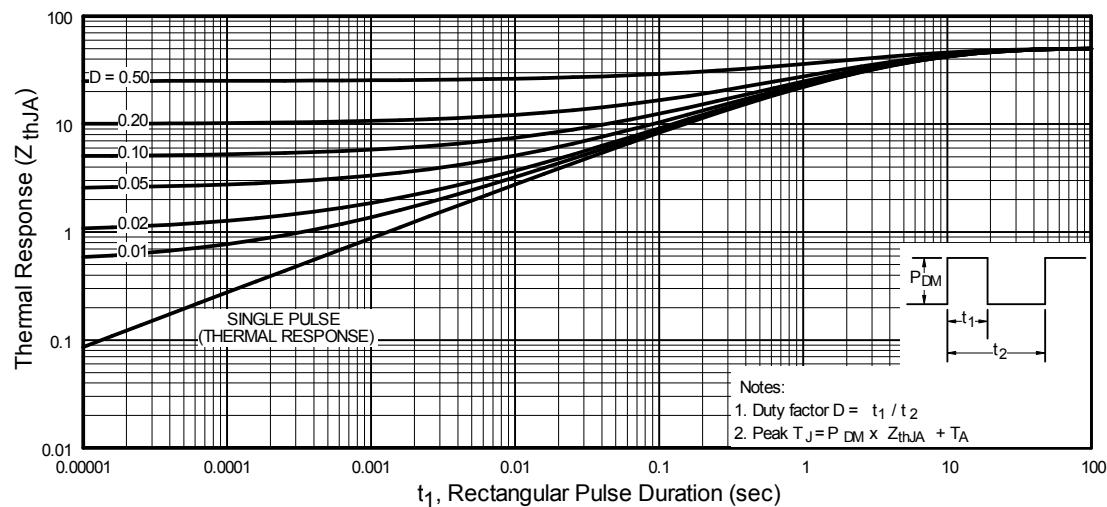
**Fig 9.** Maximum Drain Current vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



**Fig 10b.** Switching Time Waveforms



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

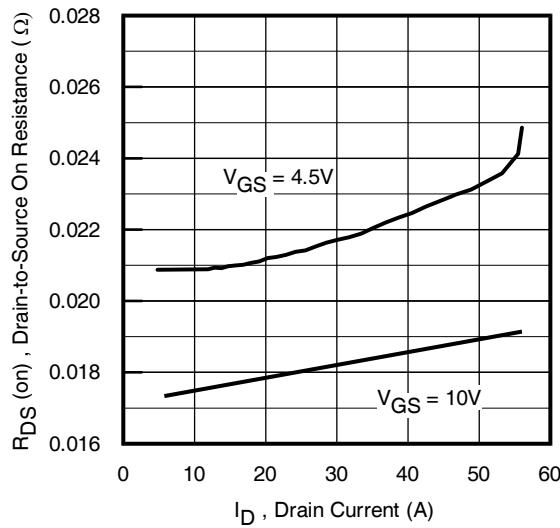


Fig 12. Typical On-Resistance Vs.  
Drain Current

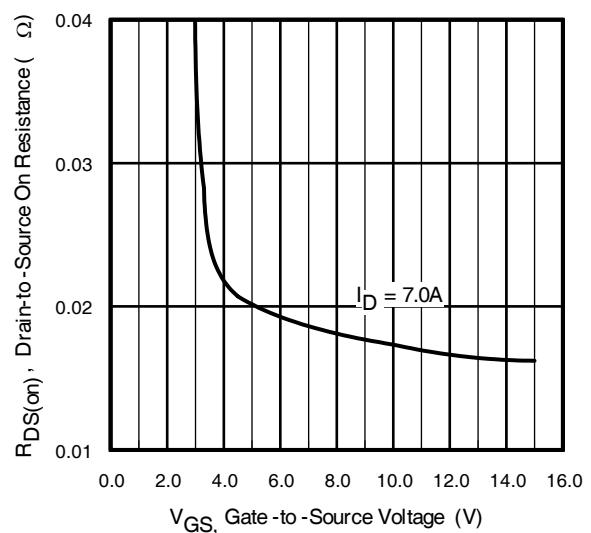


Fig 13. Typical On-Resistance Vs.  
Gate Voltage

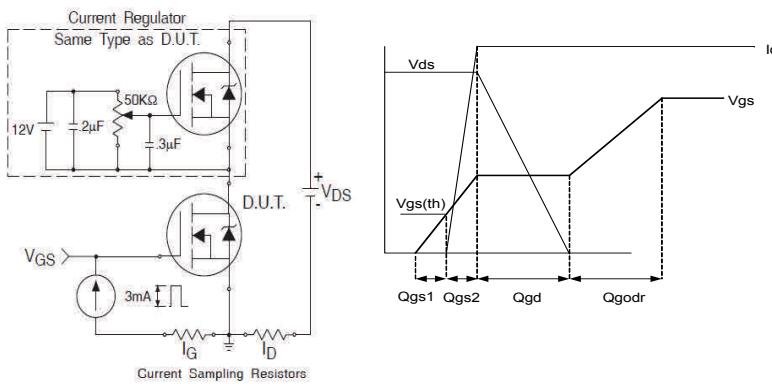


Fig 14a&b. Basic Gate Charge Test Circuit  
and Waveform

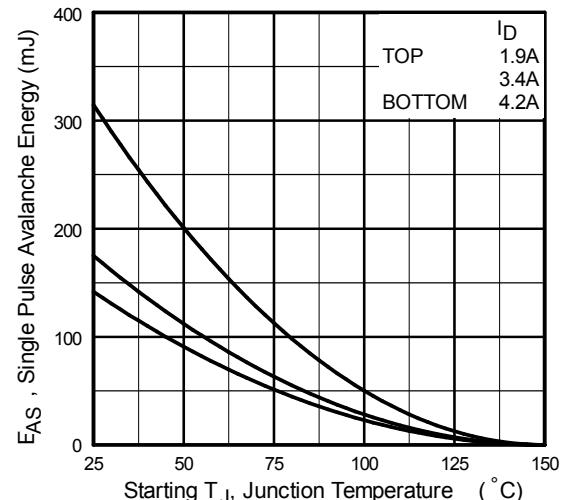


Fig 15c. Maximum Avalanche Energy  
Vs. Drain Current

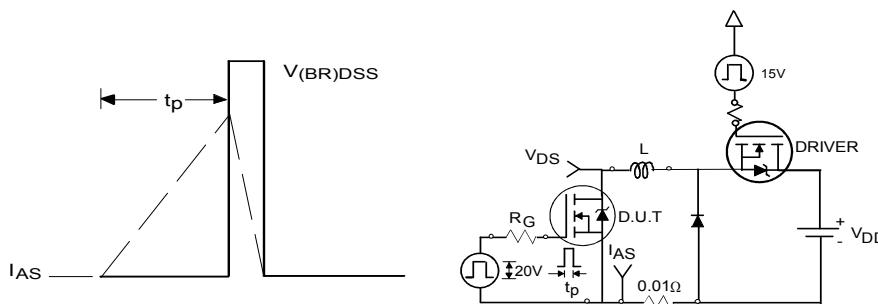
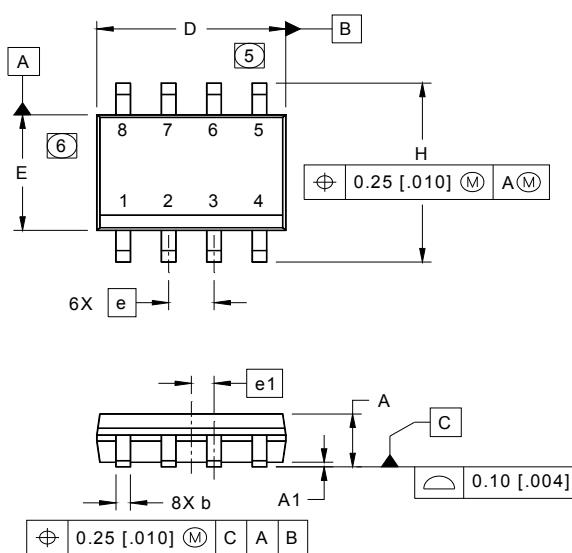


Fig 15a&b. Unclamped Inductive Test circuit  
and Waveforms

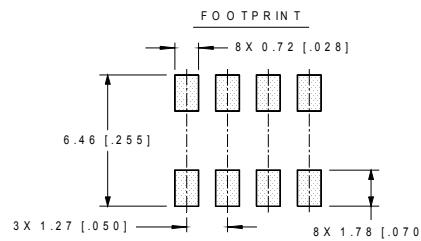
## SO-8 Package Outline (Dimensions are shown in millimeters (inches))



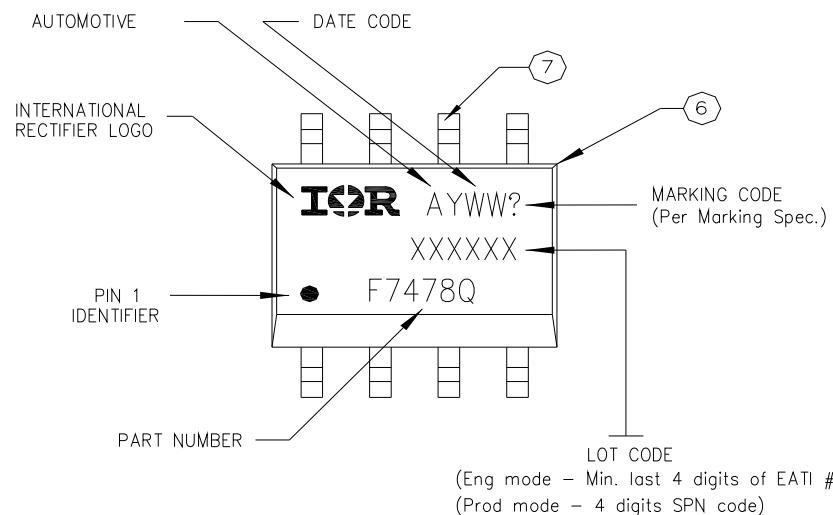
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050	BASIC	1.27	BASIC
e 1	.025	BASIC	0.635	BASIC
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

**NOTES:**

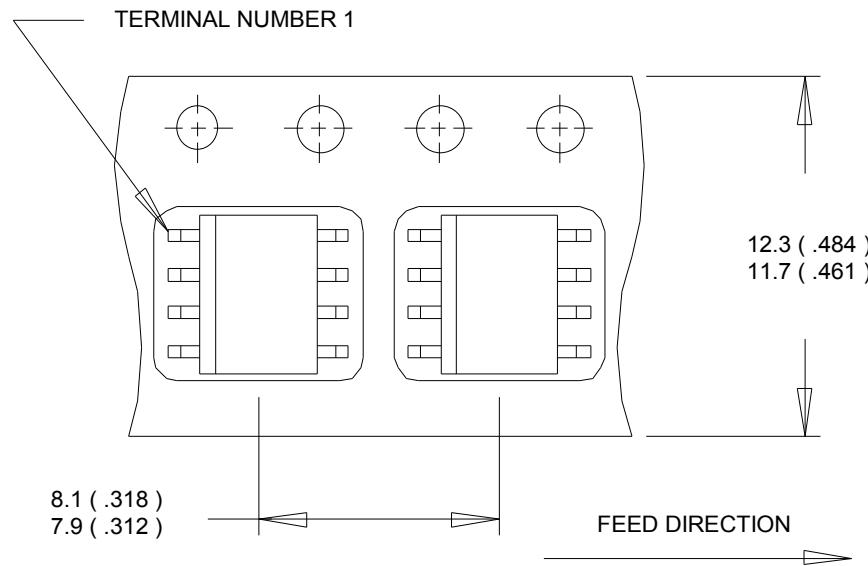
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M -1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



## SO-8 Part Marking Information

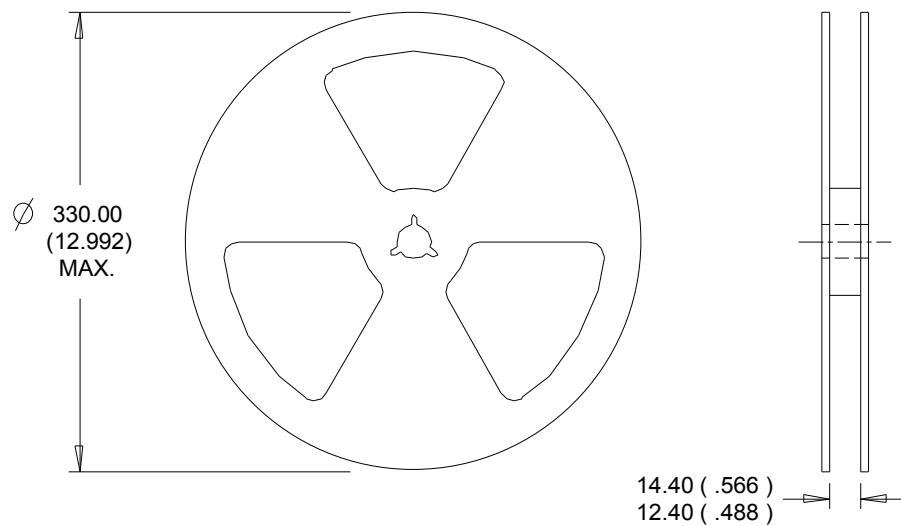


**SO-8 Tape and Reel** (Dimensions are shown in millimeters (inches))



**NOTES:**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



**NOTES :**

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

**Qualification Information**

<b>Qualification Level</b>		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>		SO-8	MSL1
<b>ESD</b>	Machine Model	Class M3 (+/- 300V) <sup>†</sup> AEC-Q101-002	
	Human Body Model	Class H1C (+/- 2000V) <sup>†</sup> AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V) <sup>†</sup> AEC-Q101-005	
<b>RoHS Compliant</b>		Yes	

<sup>†</sup> Highest passing voltage.

**Revision History**

Date	Comments
3/11/2014	<ul style="list-style-type: none"> <li>• Added "Logic Level Gate Drive" bullet in the features section on page 1</li> <li>• Updated data sheet with new IR corporate template</li> </ul>
9/30/2015	<ul style="list-style-type: none"> <li>• Updated datasheet with corporate template</li> <li>• Corrected ordering table on page 1.</li> </ul>

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ООО "ЛайфЭлектроникс"

"LifeElectronics" LLC

ИНН 7805602321 КПП 780501001 Р/С 40702810122510004610 ФАКБ "АБСОЛЮТ БАНК" (ЗАО) в г.Санкт-Петербурге К/С 30101810900000000703 БИК 044030703

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибуторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибуторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помочь разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



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Email: org@lifeelectronics.ru